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Kind regards,

Team Nexperia



PMEG6002ELD

60 V, 0.2 A low VF MEGA Schottky barrier rectifier

5 February 2014

Product data sheet

1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a leadless ultra small SOD882D (DFN1006D-2) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

2. Features and benefits

- Average forward current: $I_{F(AV)} \leq 0.2$ A
- Reverse voltage: $V_R \leq 60$ V
- Low forward voltage $V_F \leq 600$ mV
- AEC-Q101 qualified
- Solderable side pads
- Package height typ. 0.37 mm

3. Applications

- LED backlight for mobile application
- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Low power consumption applications

4. Quick reference data

Table 1. Quick reference data

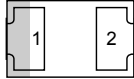

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$I_{F(AV)}$	average forward current	$\delta = 0.5$; $f = 20$ kHz; $T_{amb} \leq 130$ °C; square wave	[1]	-	-	0.2	A
		$\delta = 0.5$; $f = 20$ kHz; $T_{sp} \leq 140$ °C; square wave		-	-	0.2	A
V_R	reverse voltage	$T_j = 25$ °C		-	-	60	V
V_F	forward voltage	$I_F = 200$ mA; pulsed; $t_p \leq 300$ μ s; $\delta \leq 0.02$; $T_j = 25$ °C		-	540	600	mV
I_R	reverse current	$V_R = 10$ V; pulsed; $t_p \leq 2$ ms; $\delta \leq 0.02$; $T_j = 25$ °C		-	2	10	μ A

[1] Device mounted on a ceramic PCB, Al_2O_3 , standard footprint.



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode ^[1]	 <p>Transparent top view</p> <p>DFN1006D-2 (SOD882D)</p>	 <p>sym001</p>
2	A	anode		

[1] The marking bar indicates the cathode.

6. Ordering information

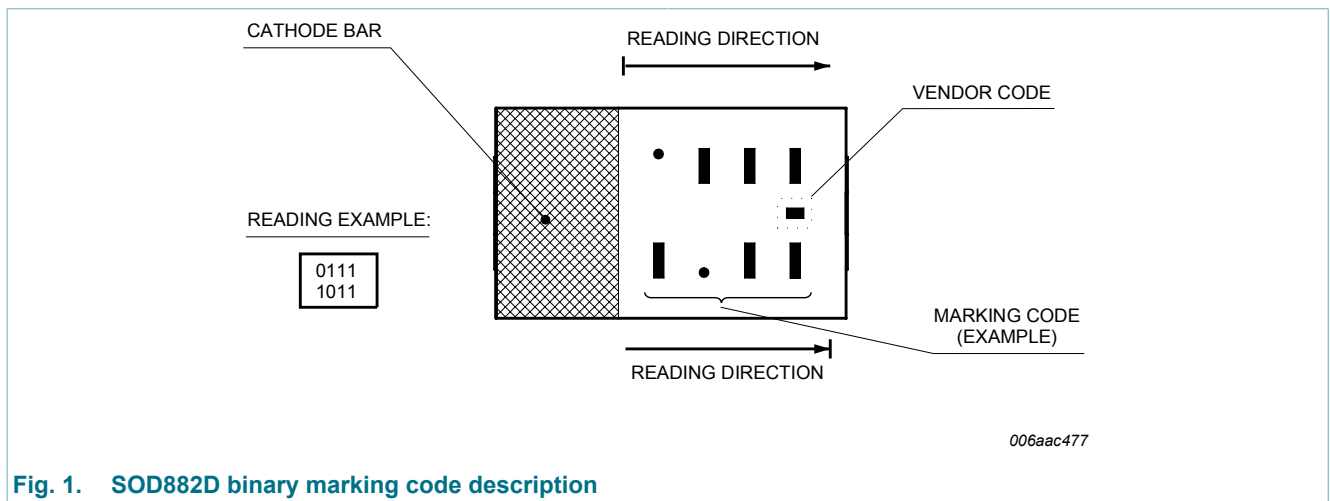
Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMEG6002ELD	DFN1006D-2	DFN1006D-2: leadless ultra small plastic package; 2 terminals	SOD882D

7. Marking

Table 4. Marking codes

Type number	Marking code
PMEG6002ELD	1111 1010



8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_R	reverse voltage	$T_j = 25\text{ °C}$		-	60	V
I_F	forward current	$T_{sp} \leq 140\text{ °C}$		-	0.28	A
$I_{F(AV)}$	average forward current	$\delta = 0.5$; $f = 20\text{ kHz}$; $T_{amb} \leq 130\text{ °C}$; square wave	[1]	-	0.2	A
		$\delta = 0.5$; $f = 20\text{ kHz}$; $T_{sp} \leq 140\text{ °C}$; square wave		-	0.2	A
I_{FRM}	repetitive peak forward current	$t_p \leq 1\text{ ms}$; $\delta \leq 0.25$		-	1	A
I_{FSM}	non-repetitive peak forward current	$t_p = 8\text{ ms}$; $T_{j(init)} = 25\text{ °C}$; square wave		-	3	A
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	[2]	-	370	mW
			[3]	-	735	mW
			[1]	-	1090	mW
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			-55	150	°C
T_{stg}	storage temperature			-65	150	°C

[1] Device mounted on a ceramic PCB, Al_2O_3 , standard footprint.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm^2 .

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1][2]	-	-	340	K/W
			[1][3]	-	-	170	K/W
			[1][4]	-	-	115	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		[5]	-	-	20	K/W

[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm^2 .

[4] Device mounted on a ceramic PCB, Al_2O_3 , standard footprint.

[5] Soldering point of cathode tab.

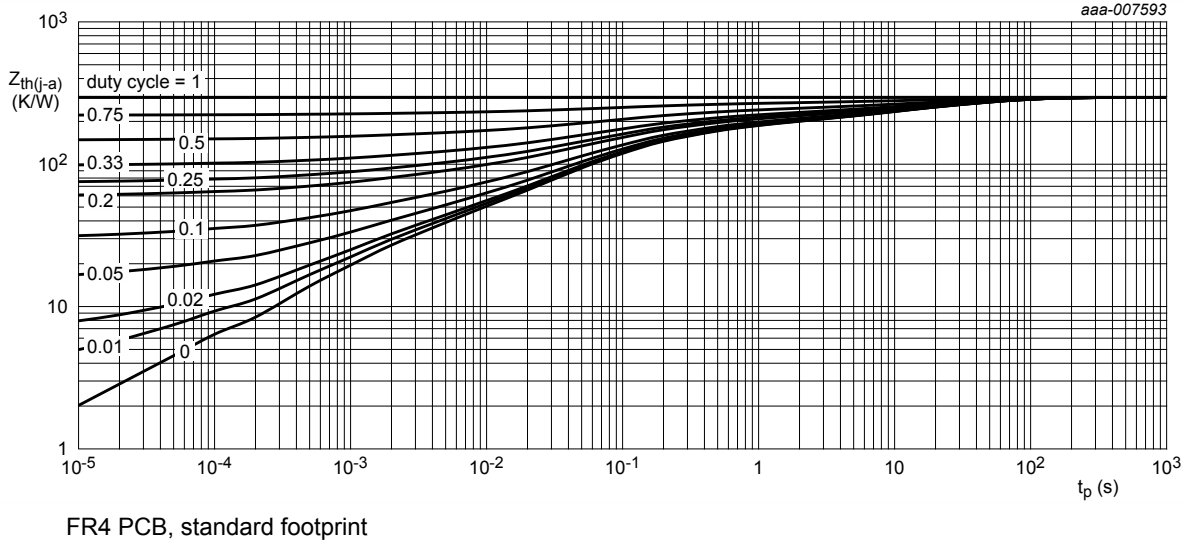


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

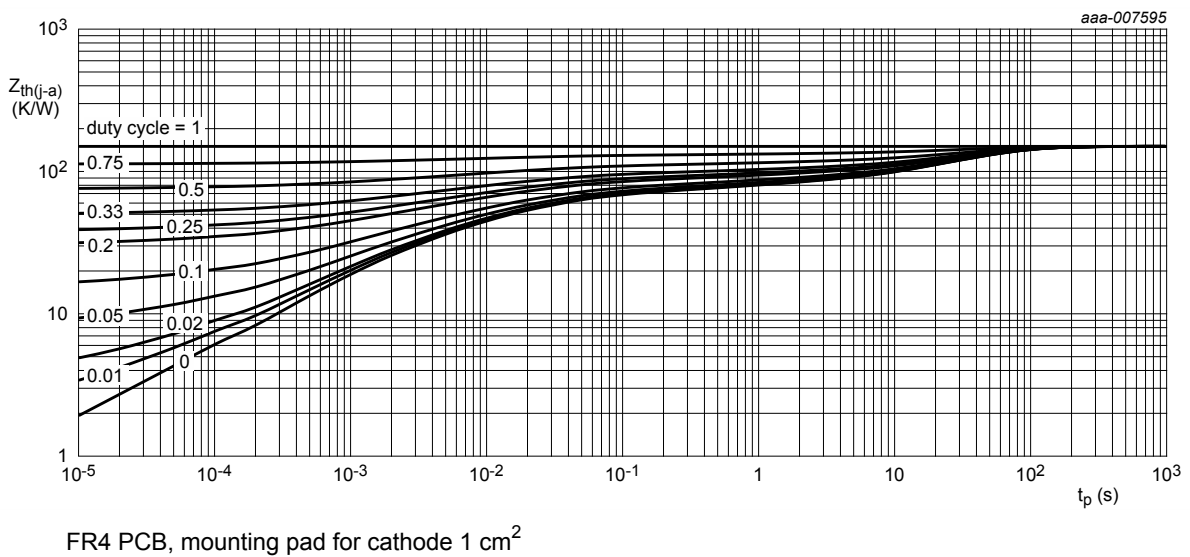
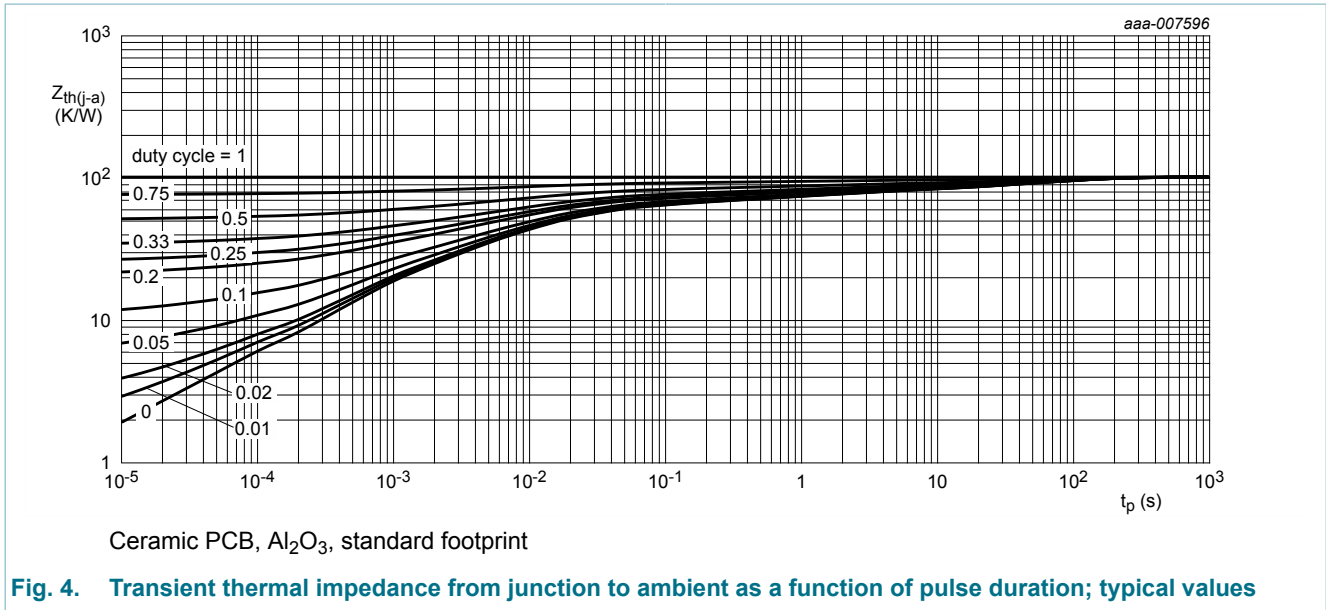


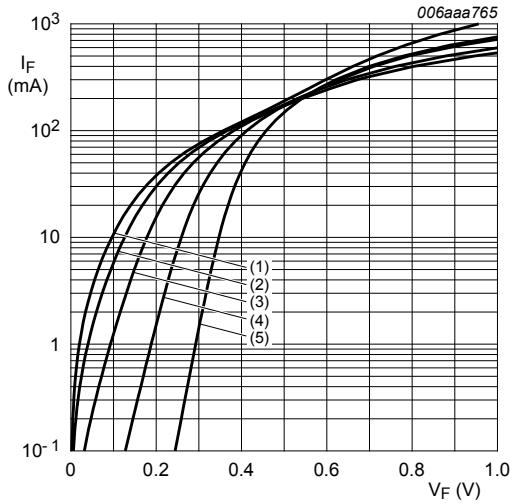
Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



10. Characteristics

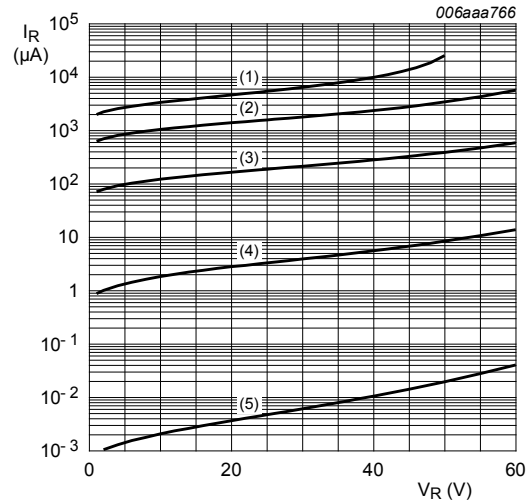
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_F	forward voltage	$I_F = 0.1 \text{ mA}$; pulsed; $t_p \leq 300 \mu\text{s}$; $\delta \leq 0.02$; $T_j = 25 \text{ }^\circ\text{C}$	-	130	170	mV
		$I_F = 1 \text{ mA}$; pulsed; $t_p \leq 300 \mu\text{s}$; $\delta \leq 0.02$; $T_j = 25 \text{ }^\circ\text{C}$	-	190	230	mV
		$I_F = 10 \text{ mA}$; pulsed; $t_p \leq 300 \mu\text{s}$; $\delta \leq 0.02$; $T_j = 25 \text{ }^\circ\text{C}$	-	260	300	mV
		$I_F = 100 \text{ mA}$; pulsed; $t_p \leq 300 \mu\text{s}$; $\delta \leq 0.02$; $T_j = 25 \text{ }^\circ\text{C}$	-	410	470	mV
		$I_F = 200 \text{ mA}$; pulsed; $t_p \leq 300 \mu\text{s}$; $\delta \leq 0.02$; $T_j = 25 \text{ }^\circ\text{C}$	-	540	600	mV
I_R	reverse current	$V_R = 10 \text{ V}$; pulsed; $t_p \leq 2 \text{ ms}$; $\delta \leq 0.02$; $T_j = 25 \text{ }^\circ\text{C}$	-	2	10	μA
		$V_R = 60 \text{ V}$; pulsed; $t_p \leq 2 \text{ ms}$; $\delta \leq 0.02$; $T_j = 25 \text{ }^\circ\text{C}$	-	20	100	μA
		$V_R = 10 \text{ V}$; pulsed; $t_p \leq 300 \mu\text{s}$; $\delta \leq 0.02$; $T_{amb} = 100 \text{ }^\circ\text{C}$	-	310	-	μA
		$V_R = 60 \text{ V}$; pulsed; $t_p \leq 300 \mu\text{s}$; $\delta \leq 0.02$; $T_{amb} = 100 \text{ }^\circ\text{C}$	-	2	-	mA
C_d	diode capacitance	$V_R = 1 \text{ V}$; $f = 1 \text{ MHz}$; $T_j = 25 \text{ }^\circ\text{C}$	-	15	20	pF
t_{rr}	reverse recovery time	$I_F = 10 \text{ mA}$; $I_R = 10 \text{ mA}$; $R_L = 100 \Omega$; $I_{R(meas)} = 1 \text{ mA}$; $T_j = 25 \text{ }^\circ\text{C}$	-	4.5	-	ns



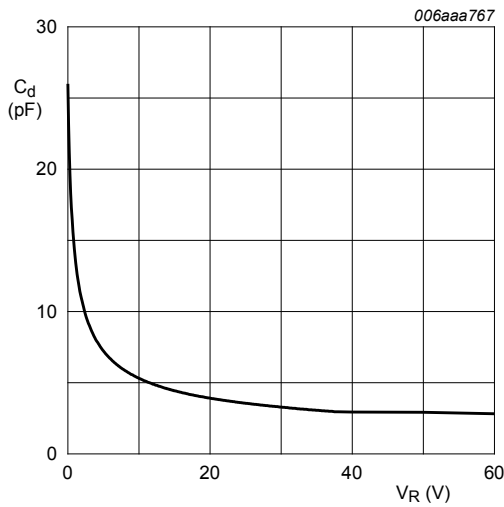
- (1) $T_j = 150\text{ }^\circ\text{C}$
- (2) $T_j = 125\text{ }^\circ\text{C}$
- (3) $T_j = 85\text{ }^\circ\text{C}$
- (4) $T_j = 25\text{ }^\circ\text{C}$
- (5) $T_j = -40\text{ }^\circ\text{C}$

Fig. 5. Forward current as a function of forward voltage; typical values



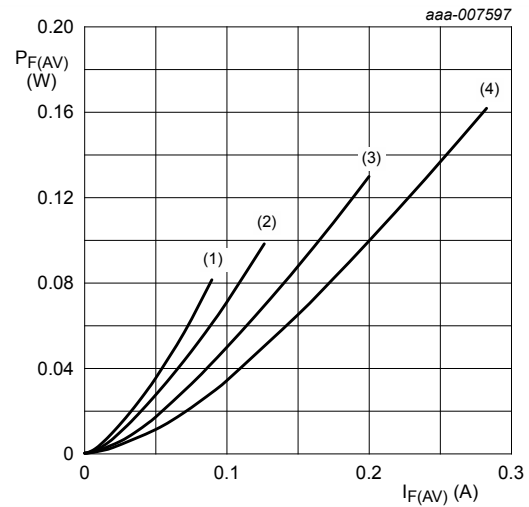
- (1) $T_j = 150\text{ }^\circ\text{C}$
- (2) $T_j = 125\text{ }^\circ\text{C}$
- (3) $T_j = 85\text{ }^\circ\text{C}$
- (4) $T_j = 25\text{ }^\circ\text{C}$
- (5) $T_j = -40\text{ }^\circ\text{C}$

Fig. 6. Reverse current as a function of reverse voltage; typical values



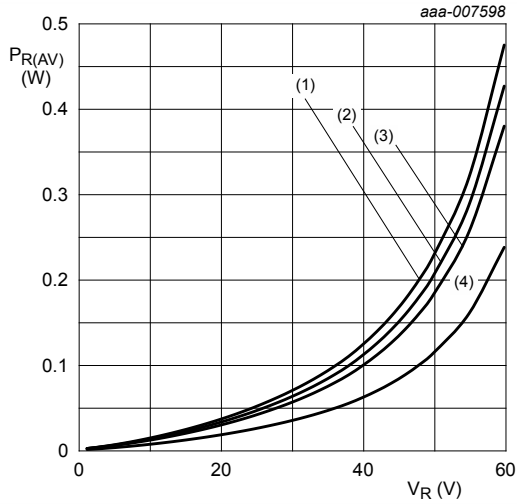
$f = 1\text{ MHz}; T_{amb} = 25\text{ }^\circ\text{C}$

Fig. 7. Diode capacitance as a function of reverse voltage; typical values



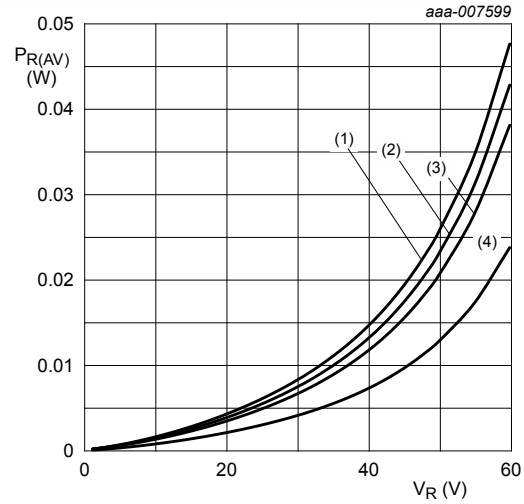
- $T_j = 150\text{ }^\circ\text{C}$
- (1) $\delta = 0.1; f = 20\text{ kHz}$
- (2) $\delta = 0.2; f = 20\text{ kHz}$
- (3) $\delta = 0.5; f = 20\text{ kHz}$
- (4) $\delta = 1\text{ (DC)}$

Fig. 8. Average forward power dissipation as a function of average forward current; typical values



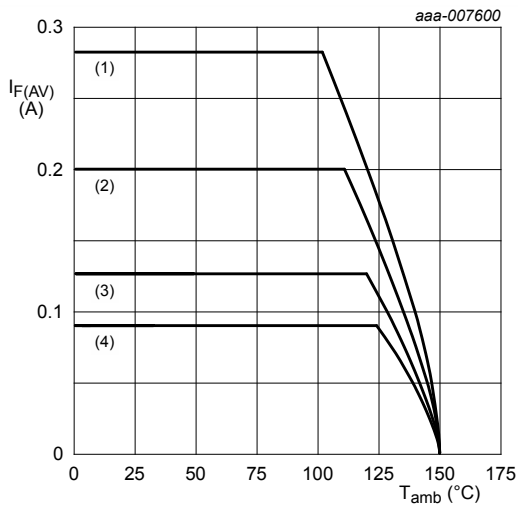
$T_j = 125\text{ °C}$
 (1) $\delta = 1$ (DC)
 (2) $\delta = 0.9$; $f = 20\text{ kHz}$
 (3) $\delta = 0.8$; $f = 20\text{ kHz}$
 (4) $\delta = 0.5$; $f = 20\text{ kHz}$

Fig. 9. Average reverse power dissipation as a function of reverse voltage; typical values



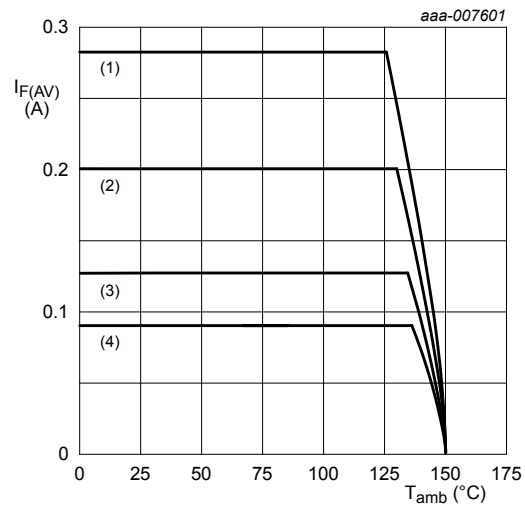
$T_j = 85\text{ °C}$
 (1) $\delta = 1$ (DC)
 (2) $\delta = 0.9$; $f = 20\text{ kHz}$
 (3) $\delta = 0.8$; $f = 20\text{ kHz}$
 (4) $\delta = 0.5$; $f = 20\text{ kHz}$

Fig. 10. Average reverse power dissipation as a function of reverse voltage; typical values



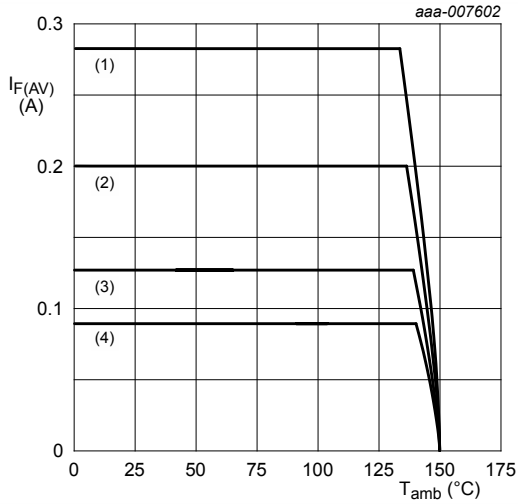
FR4 PCB, standard footprint
 $T_j = 150\text{ °C}$
 (1) $\delta = 1$ (DC)
 (2) $\delta = 0.5$; $f = 20\text{ kHz}$
 (3) $\delta = 0.2$; $f = 20\text{ kHz}$
 (4) $\delta = 0.1$; $f = 20\text{ kHz}$

Fig. 11. Average forward current as a function of ambient temperature; typical values



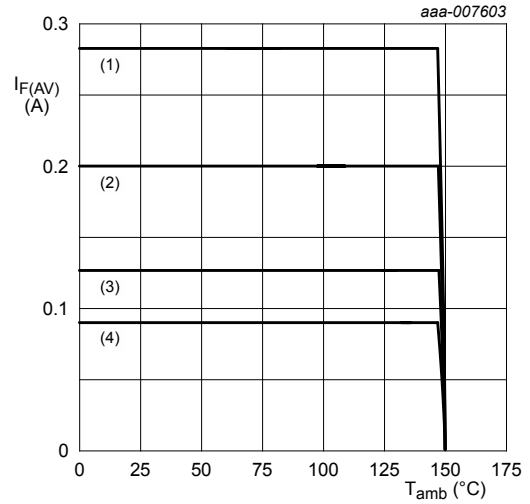
FR4 PCB, mounting pad for cathode 1 cm²
 $T_j = 150\text{ °C}$
 (1) $\delta = 1$ (DC)
 (2) $\delta = 0.5$; $f = 20\text{ kHz}$
 (3) $\delta = 0.2$; $f = 20\text{ kHz}$
 (4) $\delta = 0.1$; $f = 20\text{ kHz}$

Fig. 12. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al₂O₃, standard footprint
 T_j = 150 °C
 (1) δ = 1 (DC)
 (2) δ = 0.5; f = 20 kHz
 (3) δ = 0.2; f = 20 kHz
 (4) δ = 0.1; f = 20 kHz

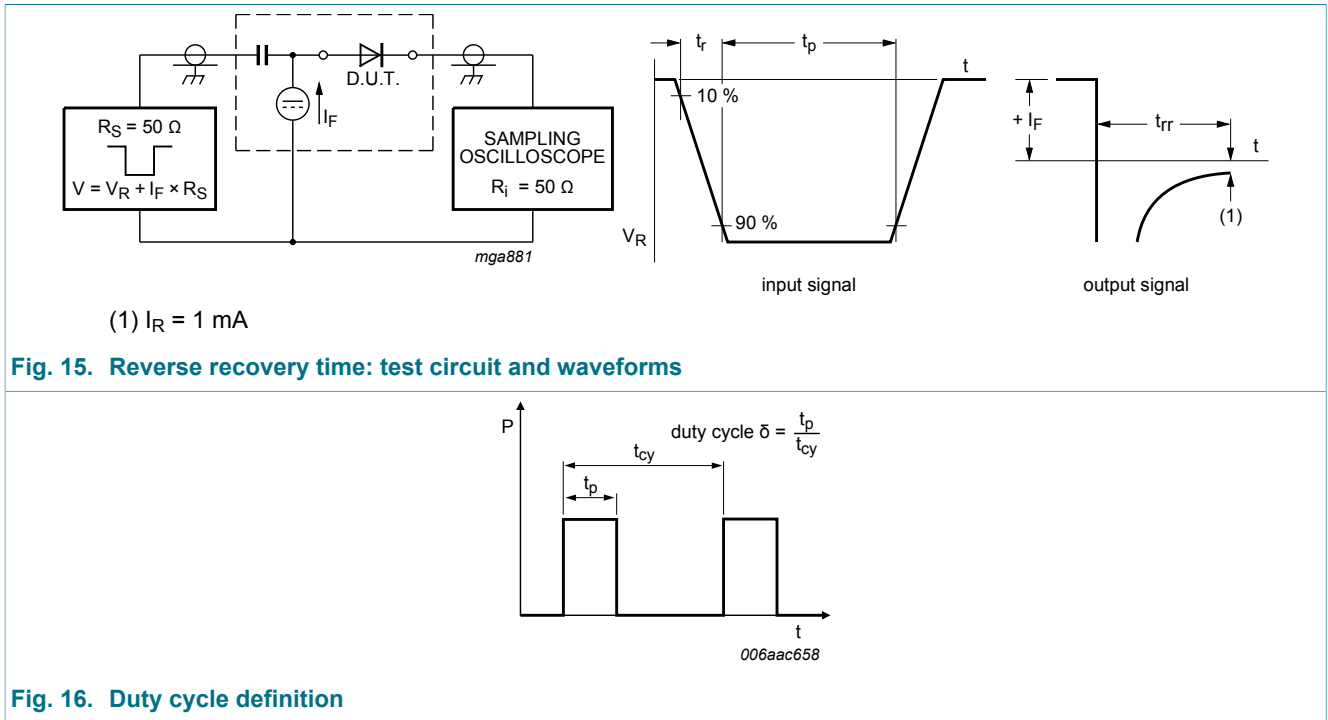
Fig. 13. Average forward current as a function of ambient temperature; typical values



T_j = 150 °C
 (1) δ = 1 (DC)
 (2) δ = 0.5; f = 20 kHz
 (3) δ = 0.2; f = 20 kHz
 (4) δ = 0.1; f = 20 kHz

Fig. 14. Average forward current as a function of solder point temperature; typical values

11. Test information



The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline

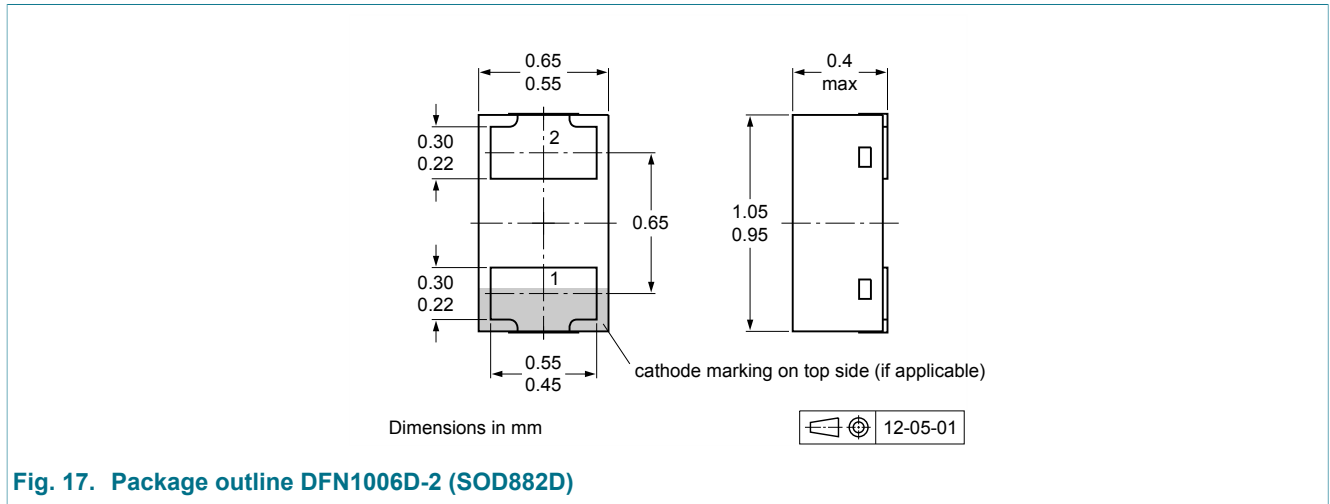


Fig. 17. Package outline DFN1006D-2 (SOD882D)

13. Soldering

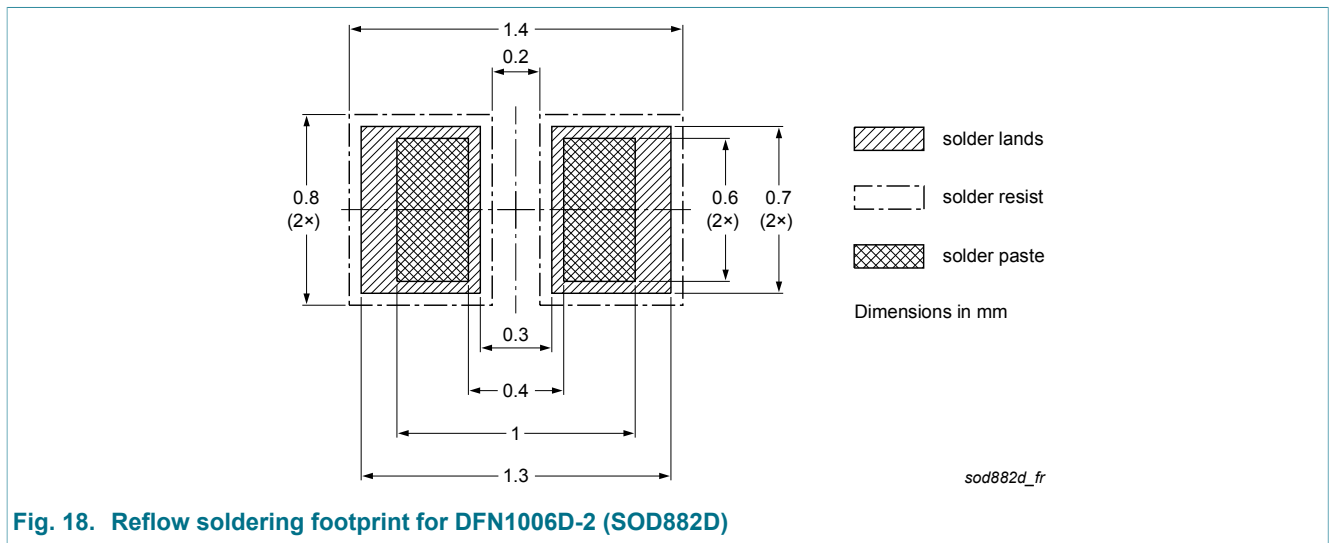


Fig. 18. Reflow soldering footprint for DFN1006D-2 (SOD882D)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG6002ELD v.3	20140205	Product data sheet	-	PMEG6002ELD v.2
Modifications:	• Table 7. Characteristics: I_R conditions corrected			
PMEG6002ELD v.2	20131210	Product data sheet	-	PMEG6002ELD v.1
PMEG6002ELD v.1	20130503	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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